

ABSTRACT

[Problem] A quartz glass crucible for pulling up a silicon single crystal, capable of forming a uniform and thin crystal layer on an inner surface by heating during a crystal pulling up step is provided.

- 5 [Solution] A quartz glass crucible 1 includes a crucible base body 10 consisting of silica glass and a crystallization accelerator-containing coating film 13 formed on the inner surface 10i of the crucible base body 10. A concentration of Fe contained in a first depth region of at least 0.5 mm or less from an inner surface 10i of the crucible base body 10 is higher than a concentration of Al contained in the first depth region.